

Sept 26, 2014 Cryptographic Hardware and Embedded Systems

Bitline PUF:

Building Native Challenge-Response PUF Capability into Any SRAM Daniel E. Holcomb Kevin Fu University of Michigan

Acknowledgment: This work was supported in part by C-FAR, one of six centers of STARnet, a Semiconductor Research Corporation program sponsored by MARCO and DARPA, and by NSF CNS-1331652. Any opinions, findings, conclusions, and recommendations expressed in these materials are those of the authors and do not necessarily reflect the views of the sponsors.

Context

CMOS PUFs

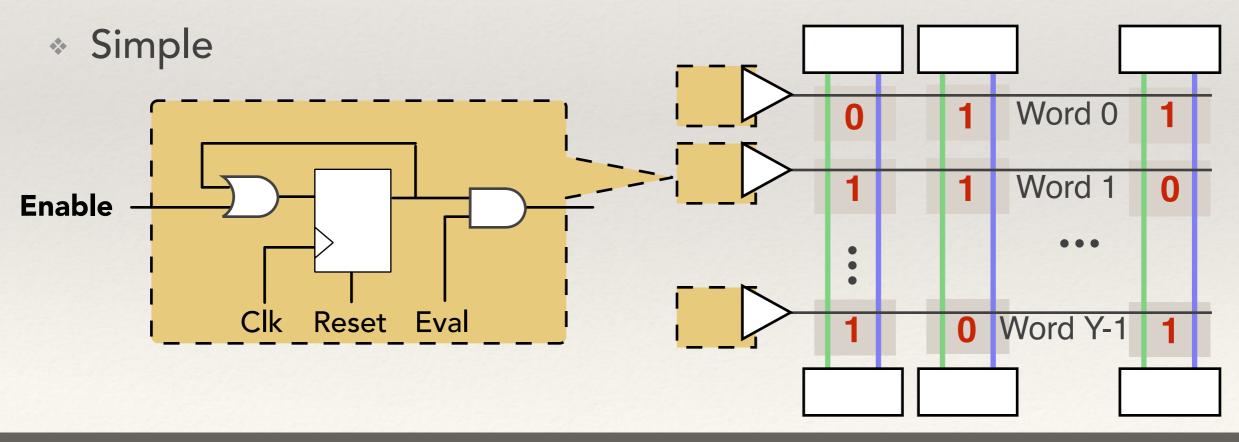
High-cost PUFs using custom circuitry

Low-cost PUFs using existing circuitry

This talk

Contributions

- Adding a few gates to wordline drivers of SRAM creates a new PUF
- Bitline PUF
 - Challenge-response operation
 - Low area overhead



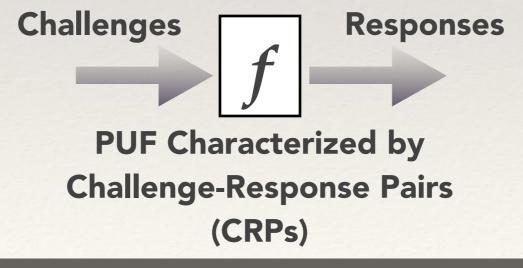
Outline

1. Introduction

- * PUFs
- * SRAM
- Bitline PUF
- 2. Evaluation
 - Uniqueness
 - Reliability
 - Modeling Attacks
- 3. Summary and Related work

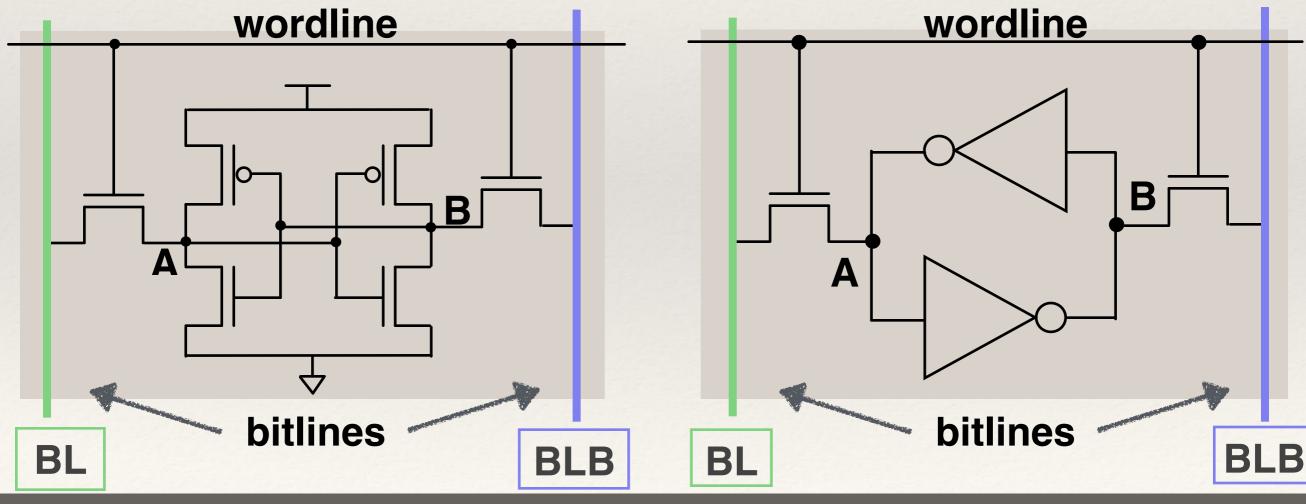
Physical Unclonable Functions (PUFs)

- Map challenges to responses according to uncontrollable physical variations
- Unique to each chip and persistent
 - Random dopant fluctuations and small devices
 - Balanced parasitics and wire lengths to avoid bias
- Applications include anti-counterfeiting and hardware metering

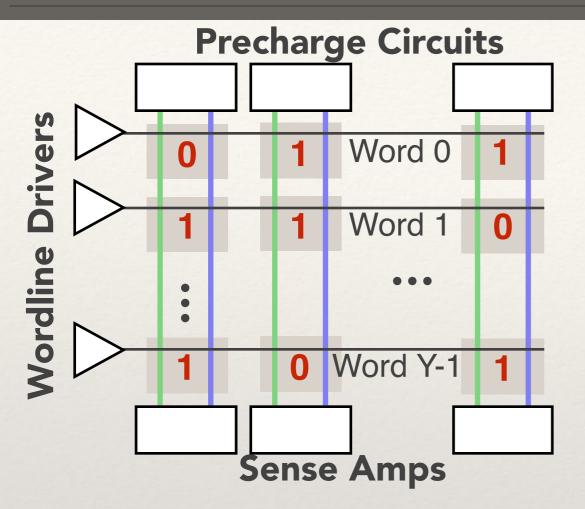


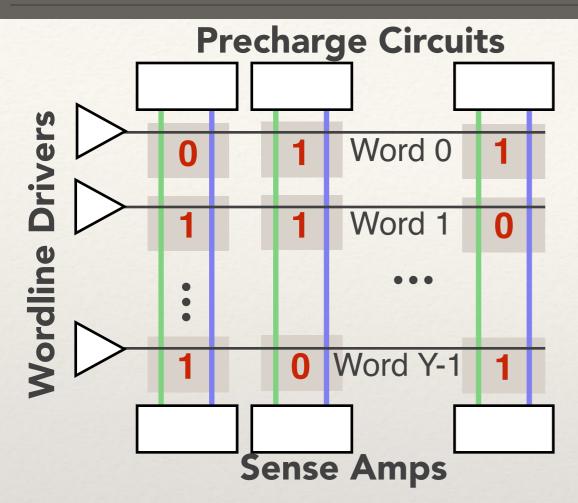
6-Transistor SRAM Cell

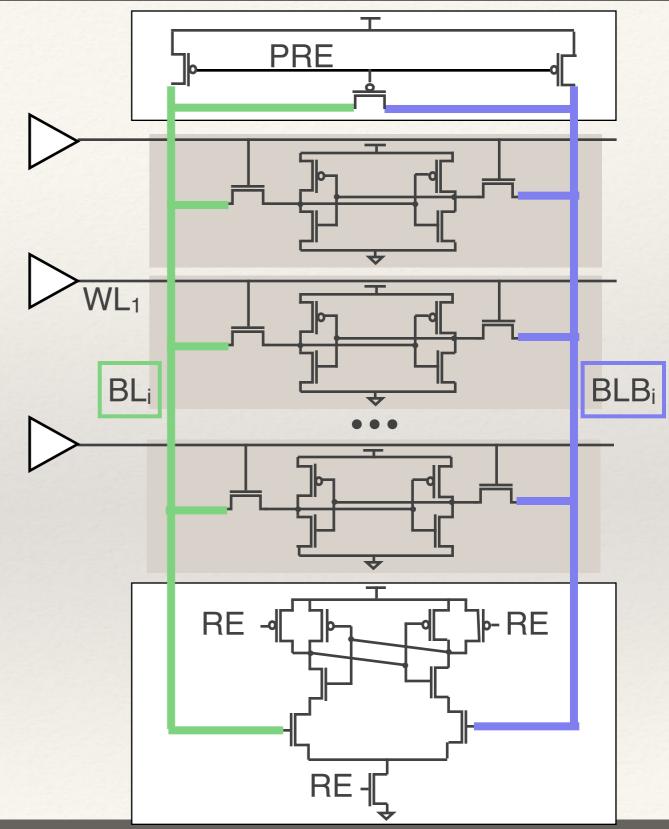
- Ubiquitous memory
- * Two stable states: "0" (AB=01) "1" (AB=10)
- * Wordline selects a cell for reading/writing
- Complementary bitlines read/write values to/from selected cells



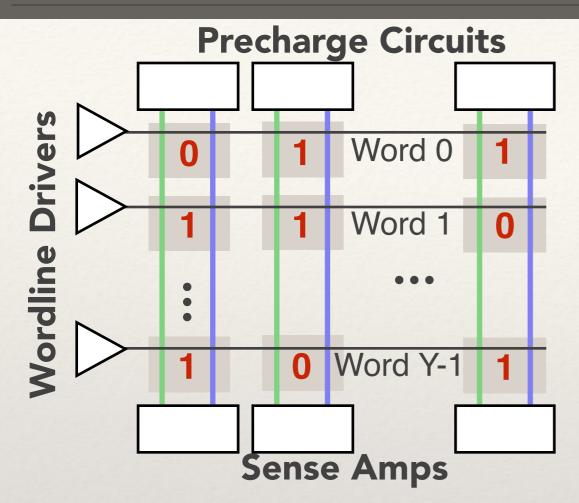
Bitline PUF — CHES 2014

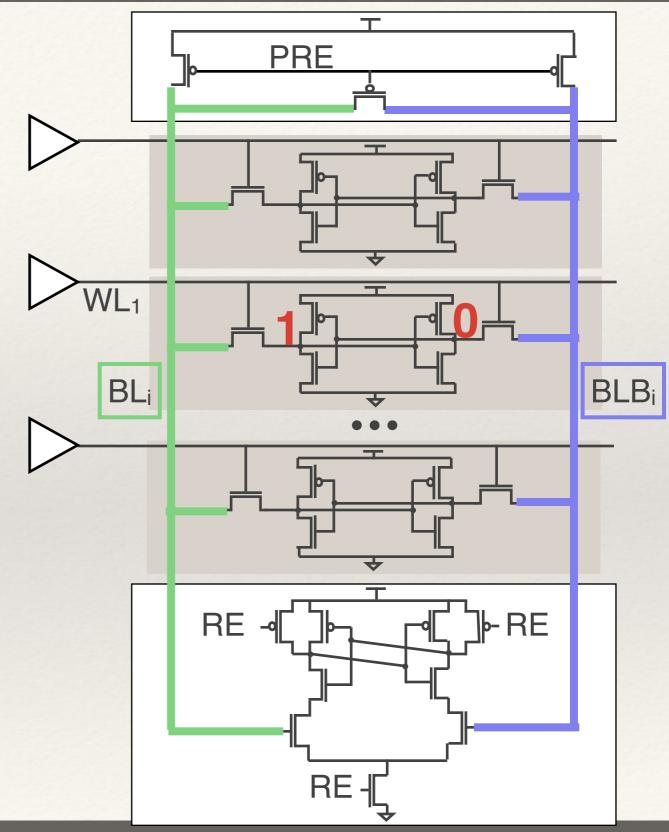




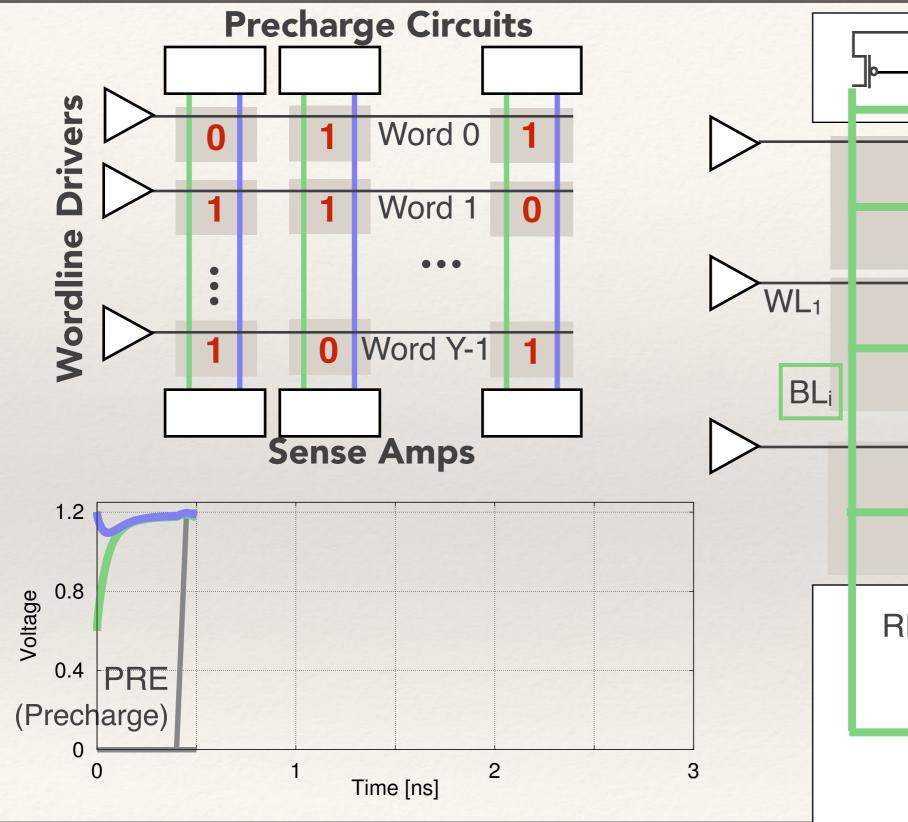


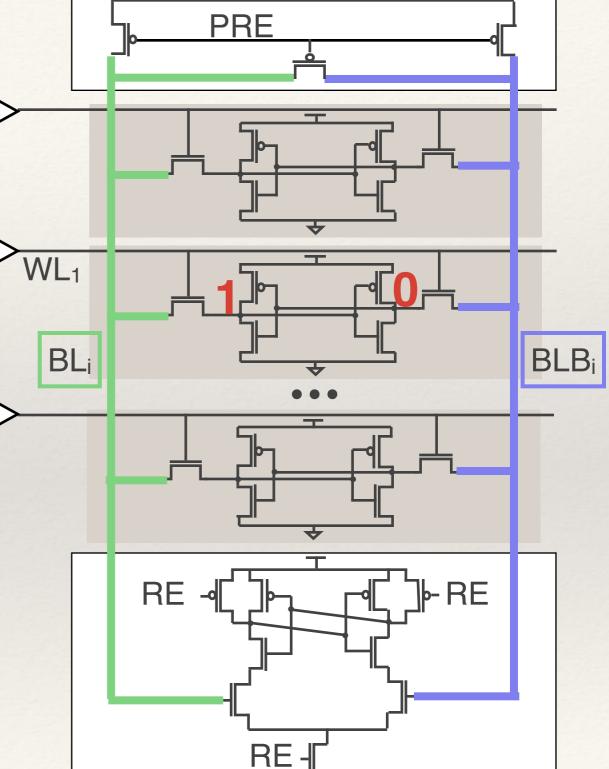
Holcomb and Fu



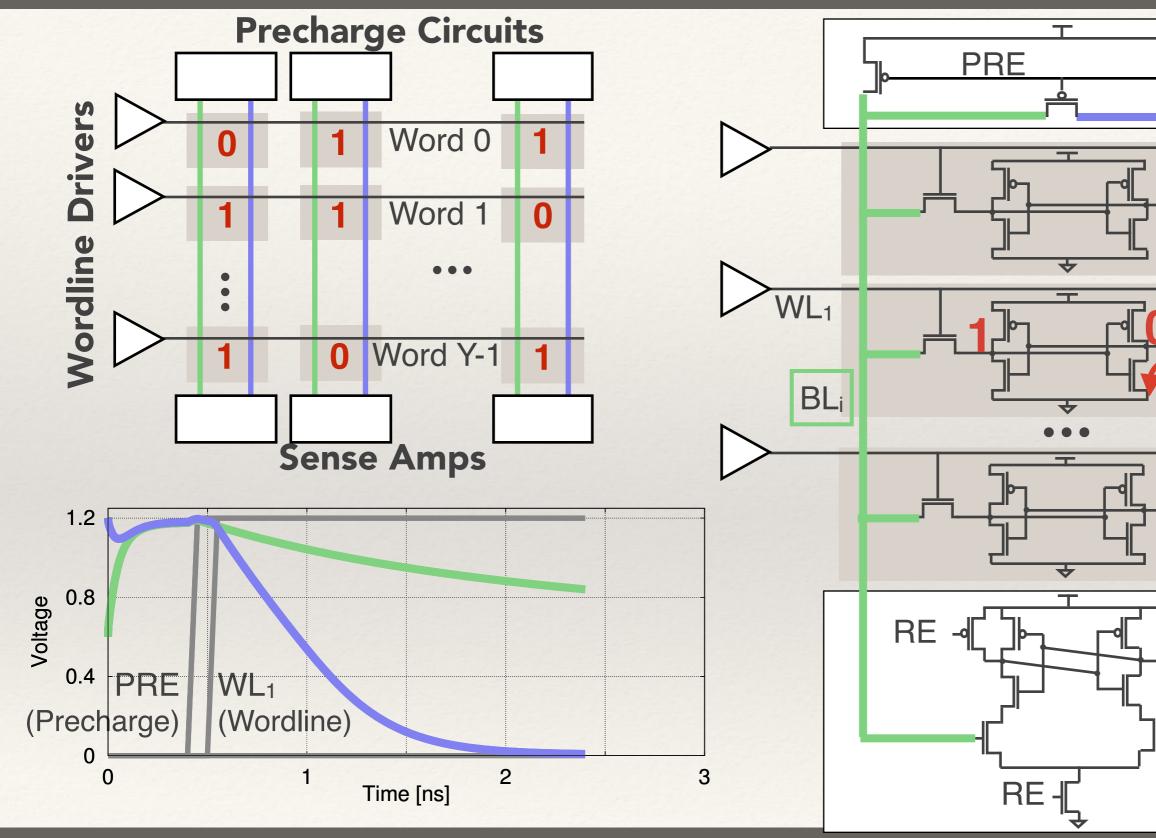


Holcomb and Fu





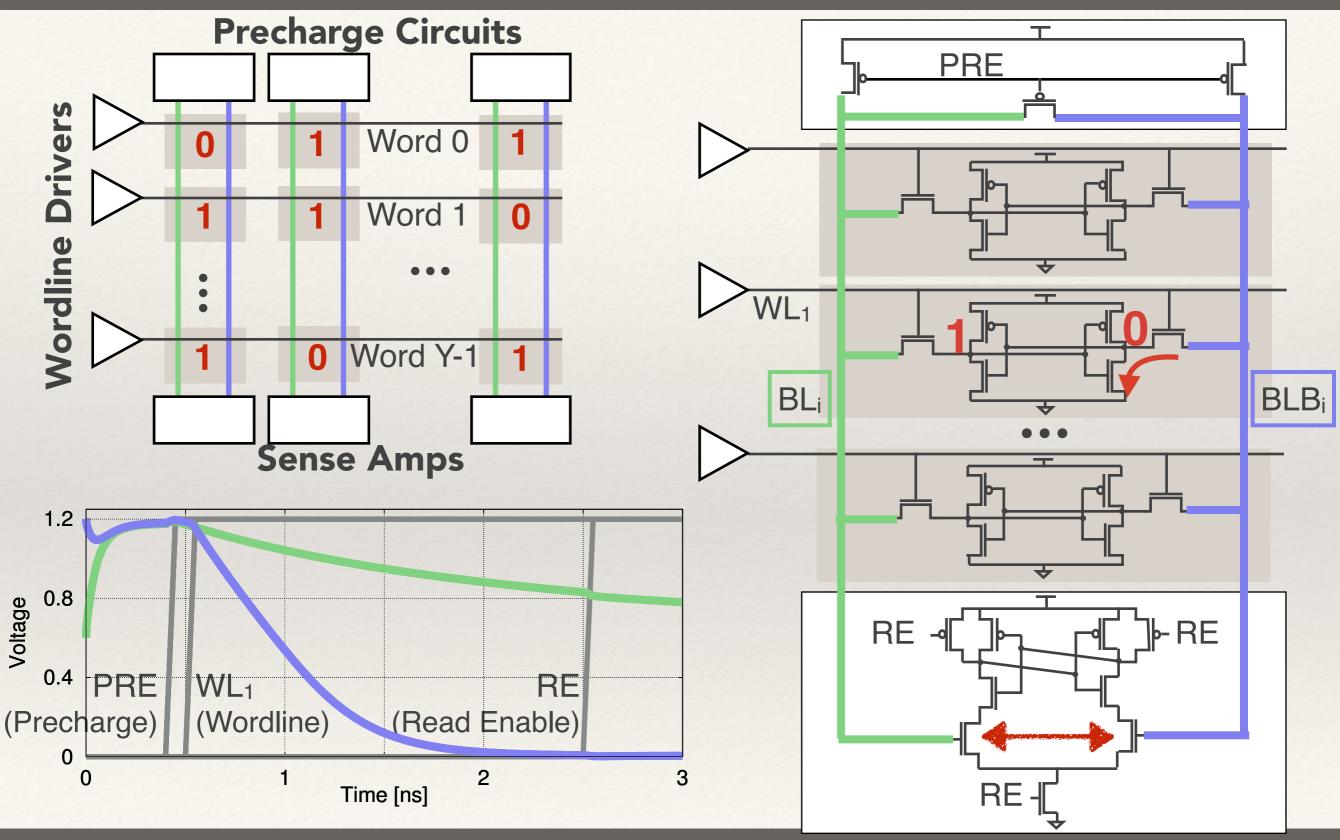
T



Bitline PUF - CHES 2014

BLB_i

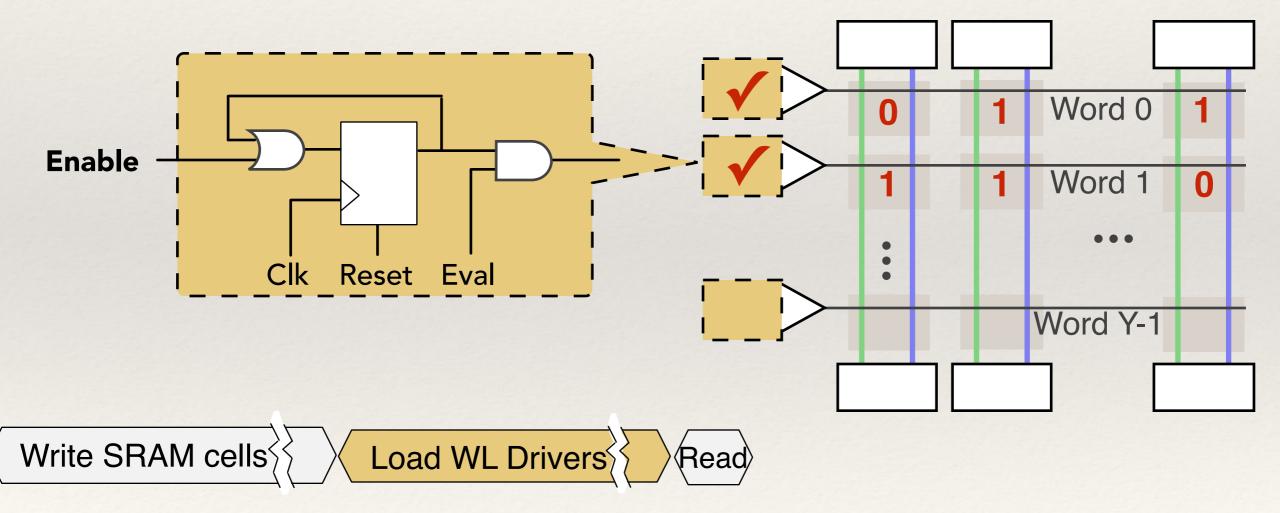
-RE



Holcomb and Fu

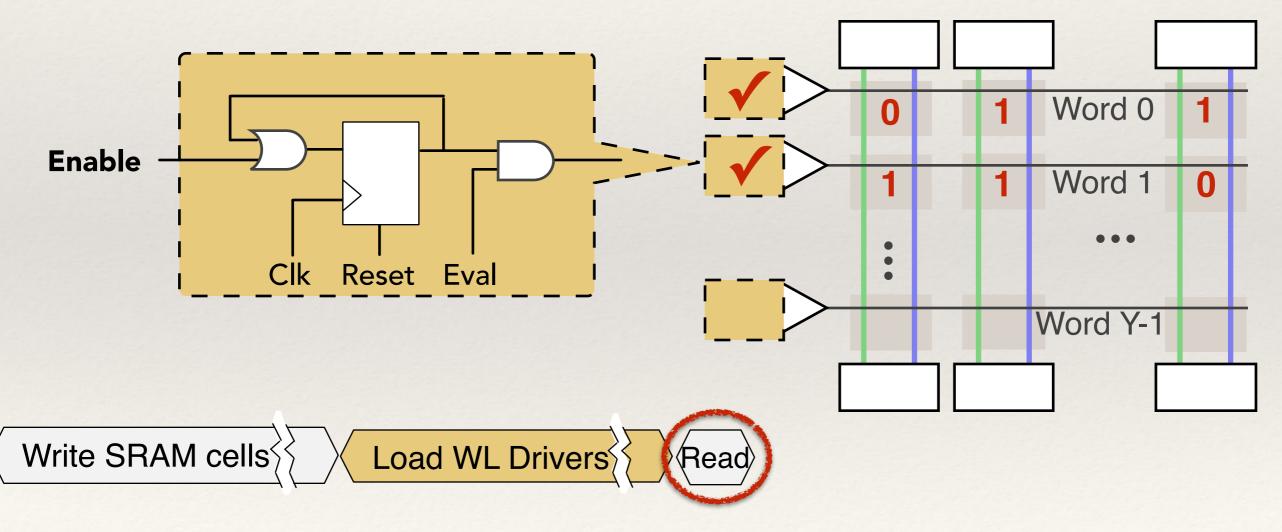
Bitline PUF

- Accumulate wordline enable signals for concurrent read
- Concurrent reading causes contention
- Contention resolves according to variations

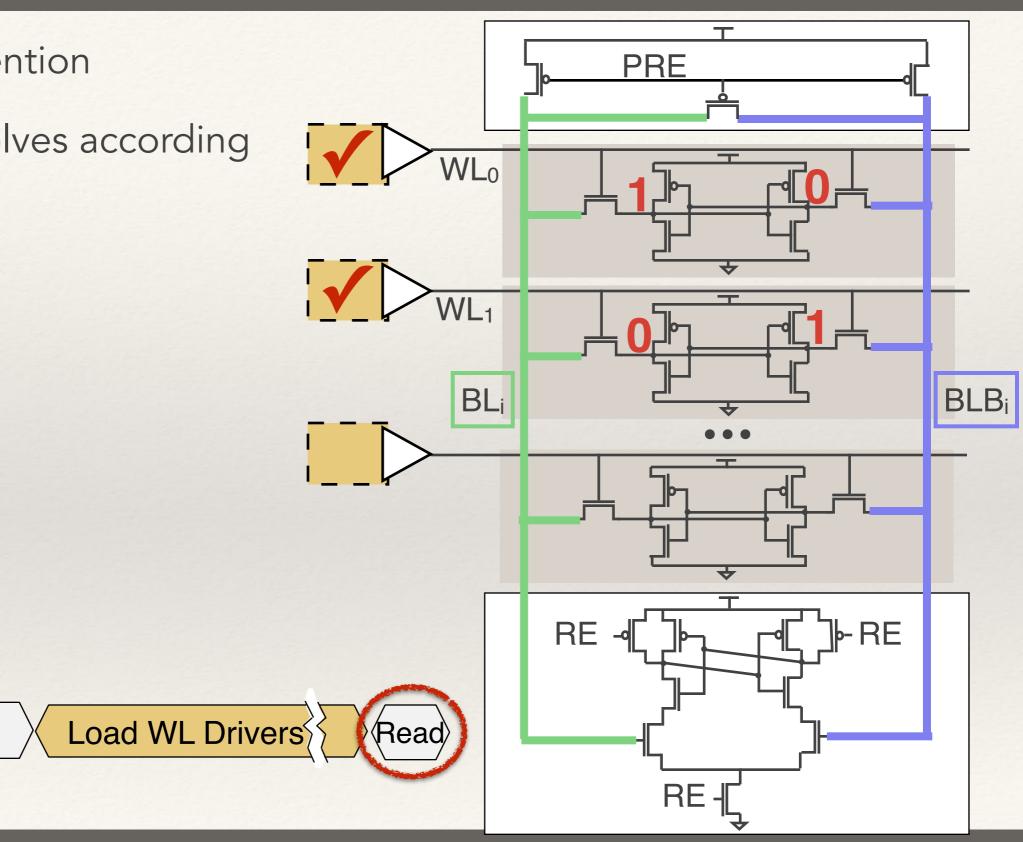


Bitline PUF

- Accumulate wordline enable signals for concurrent read
- Concurrent reading causes contention
- Contention resolves according to variations

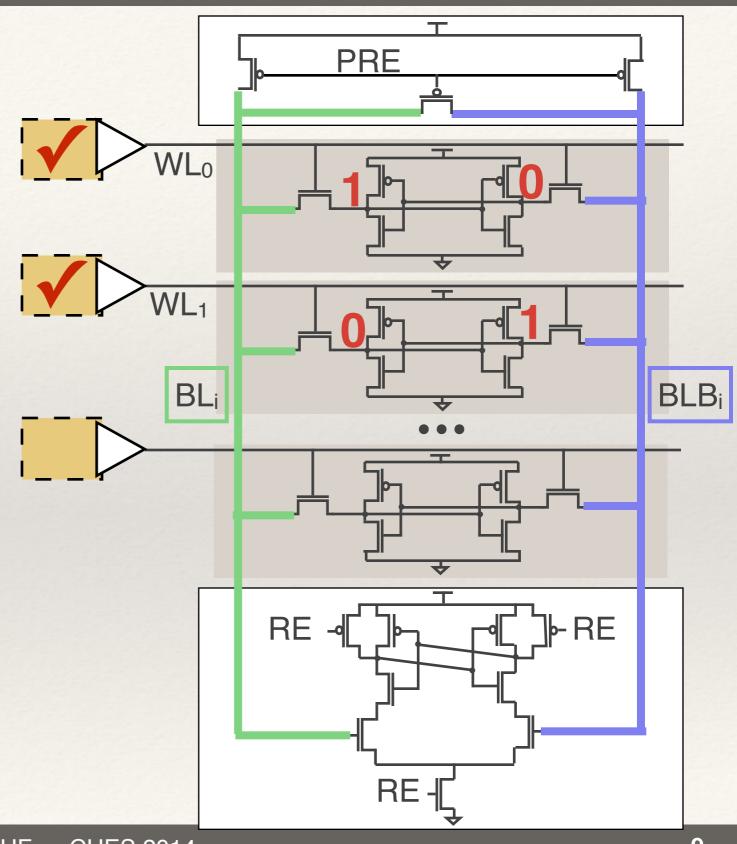


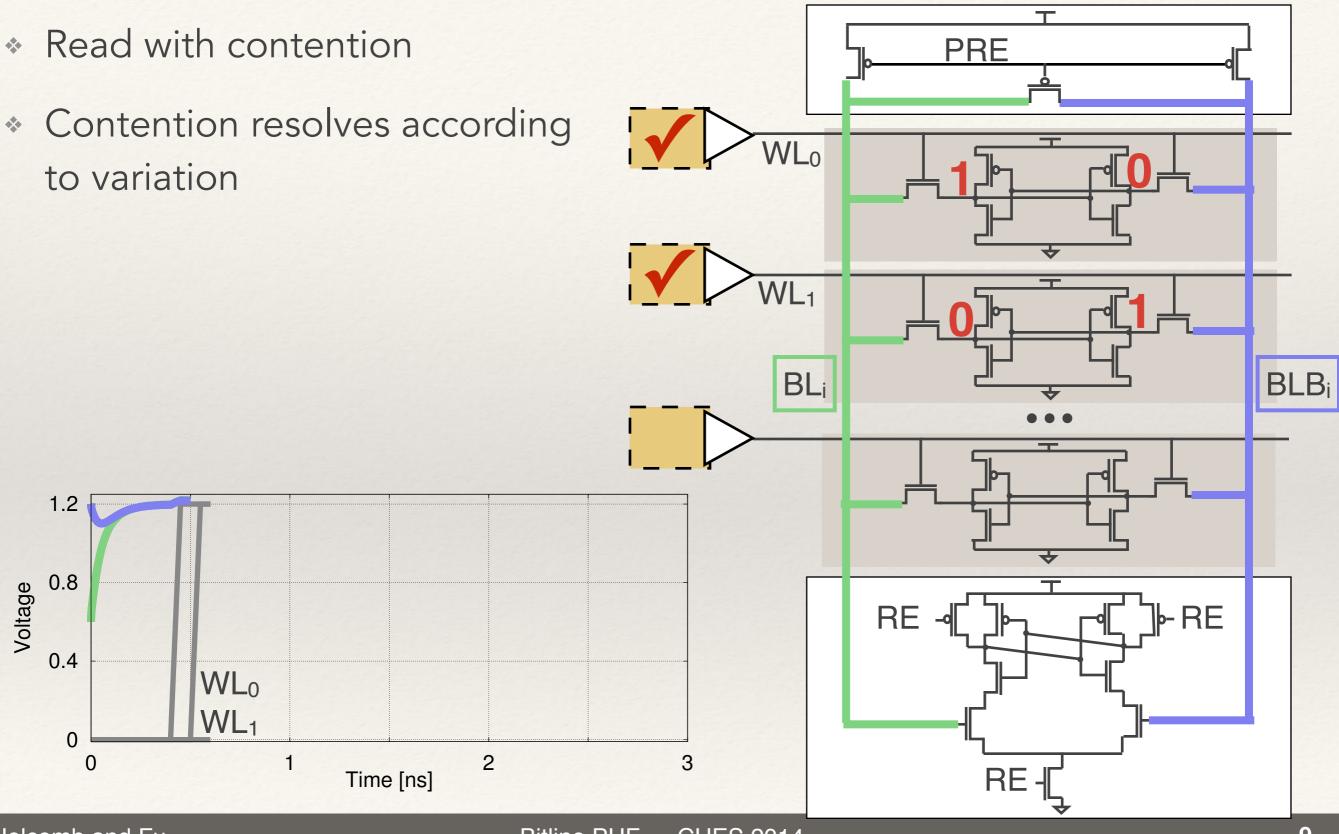
- Read with contention
- Contention resolves according to variation



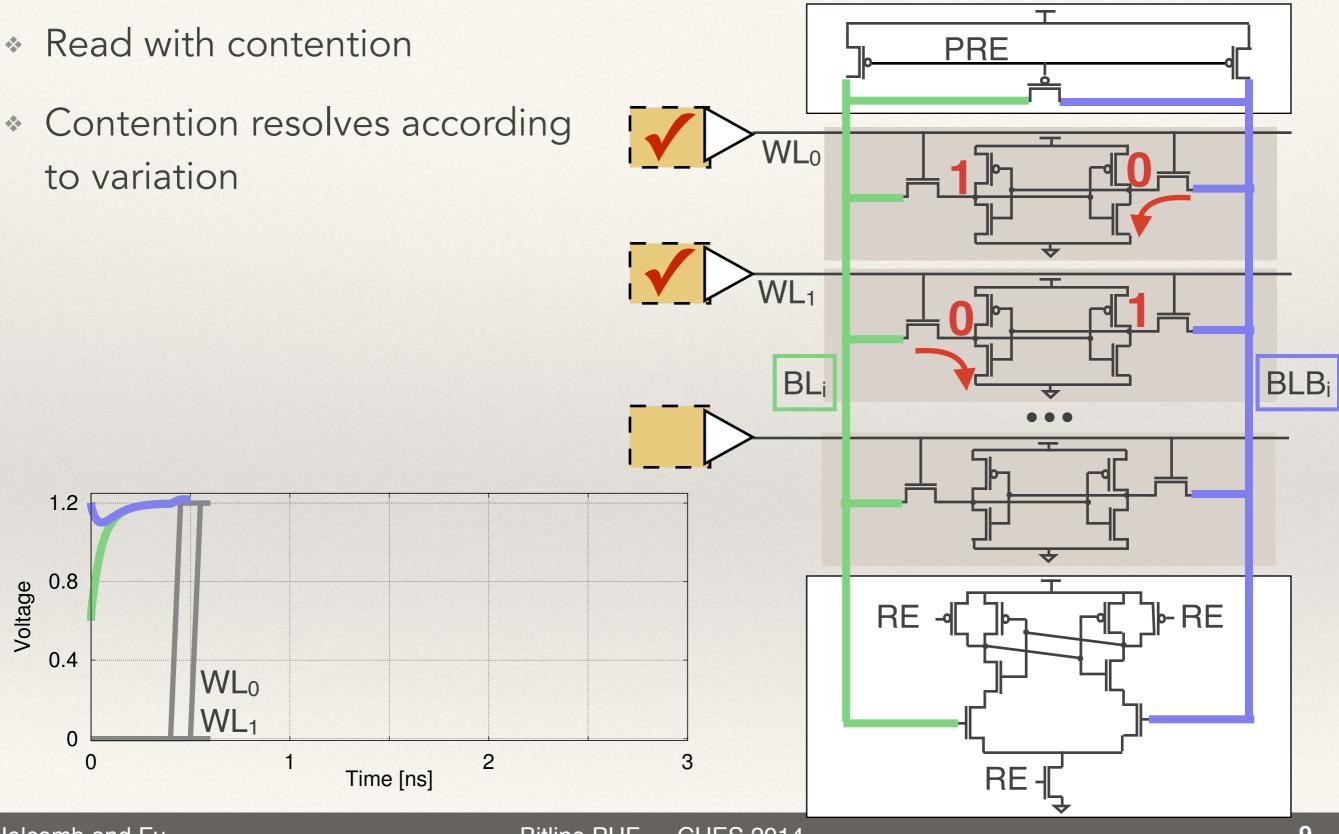
Write SRAM cells

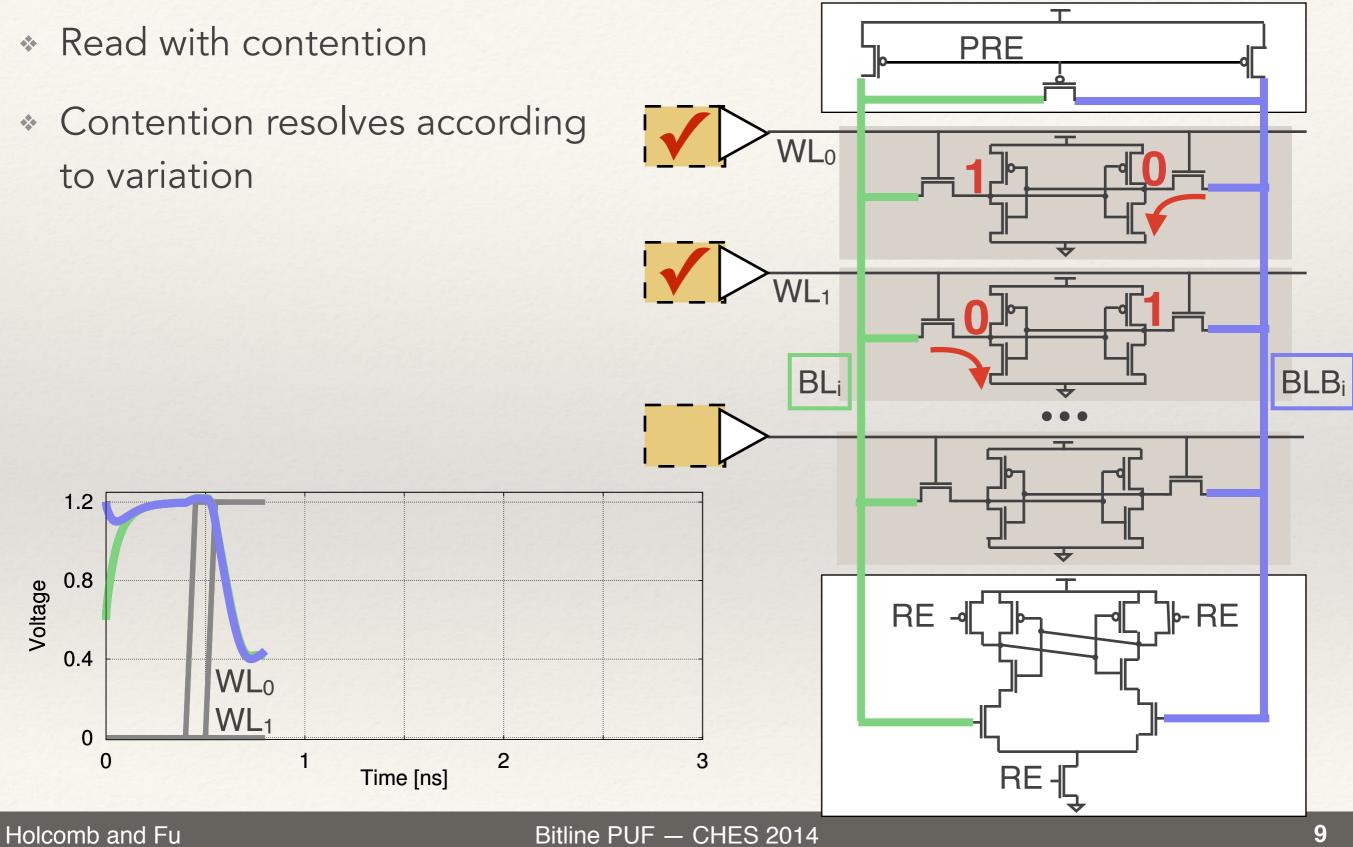
- Read with contention
- Contention resolves according to variation

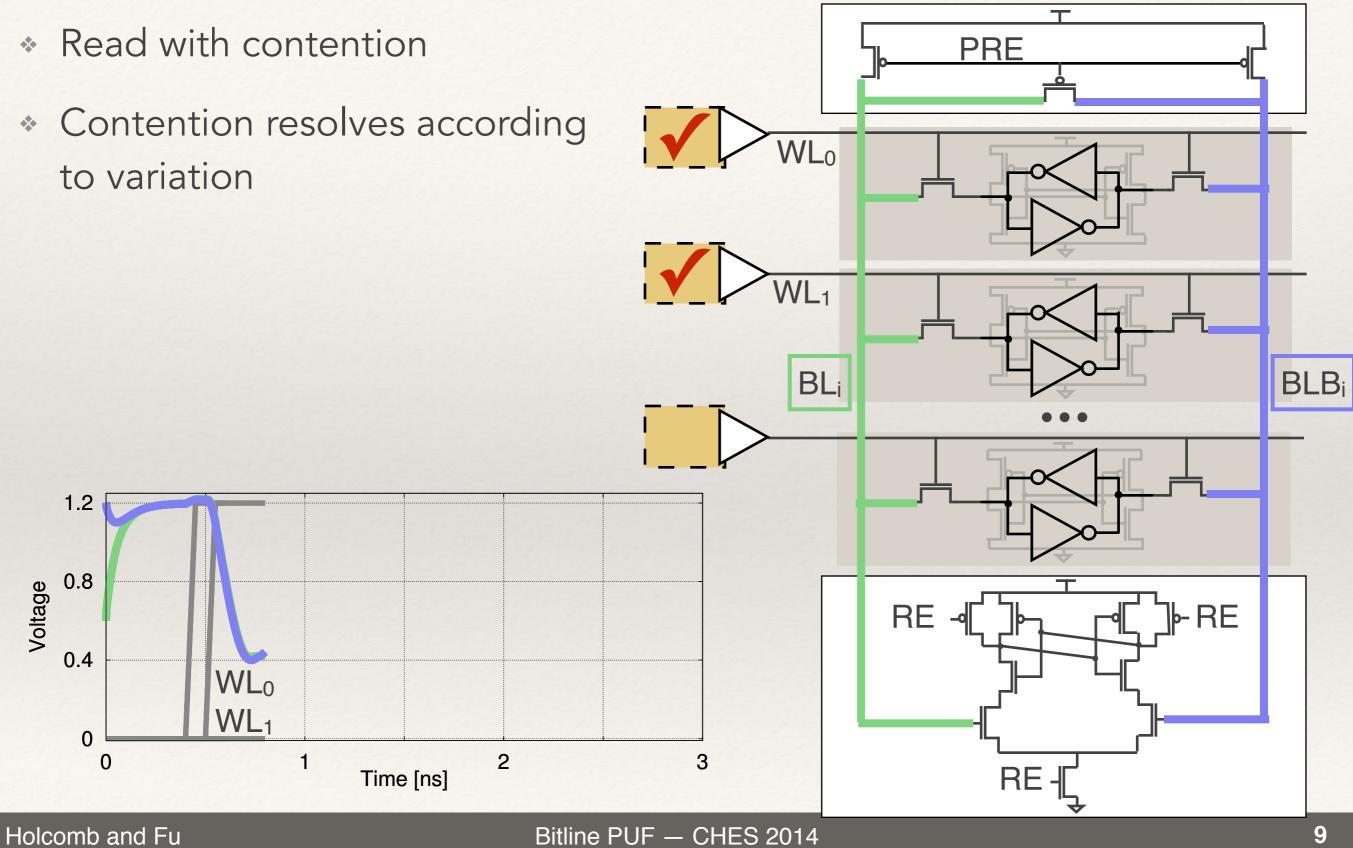


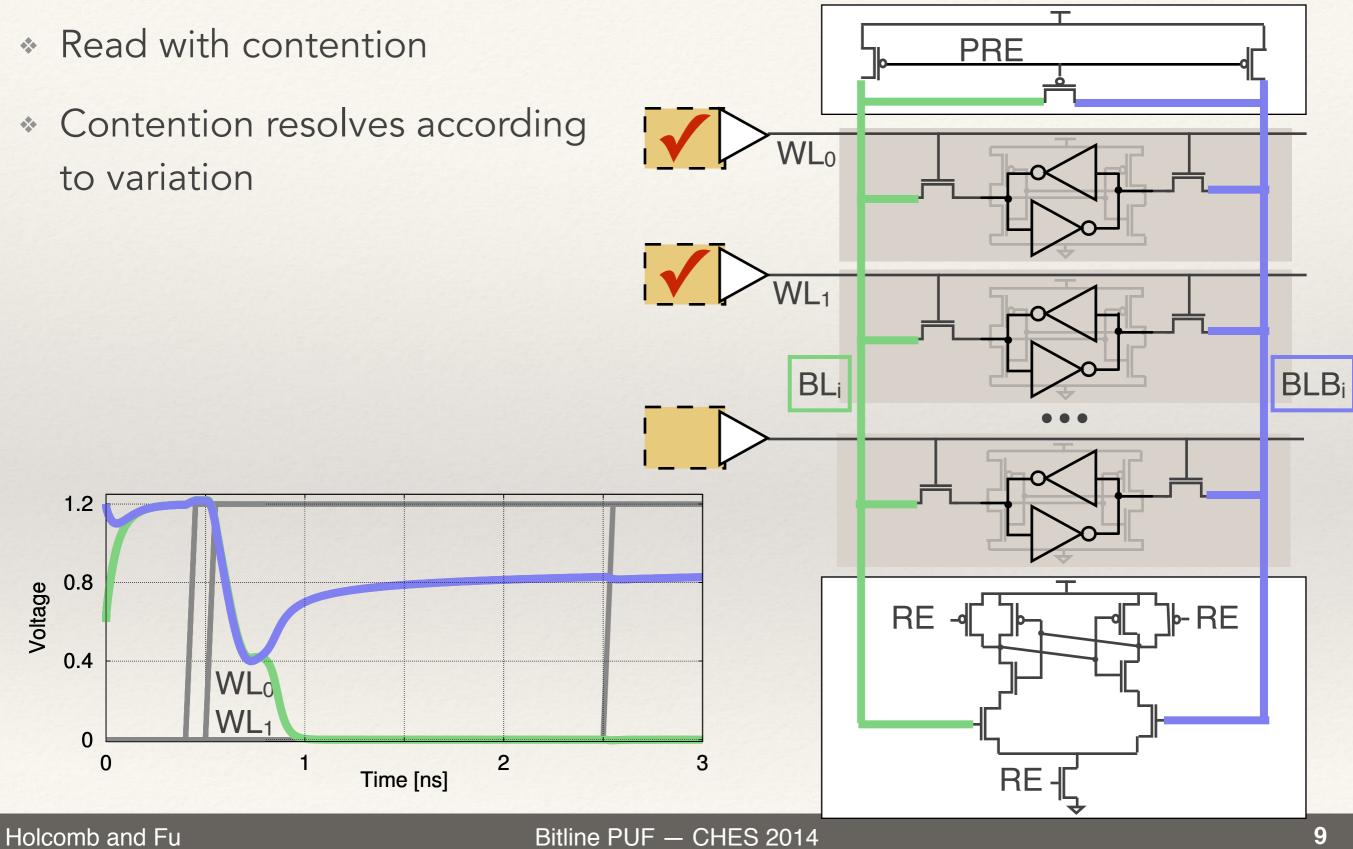


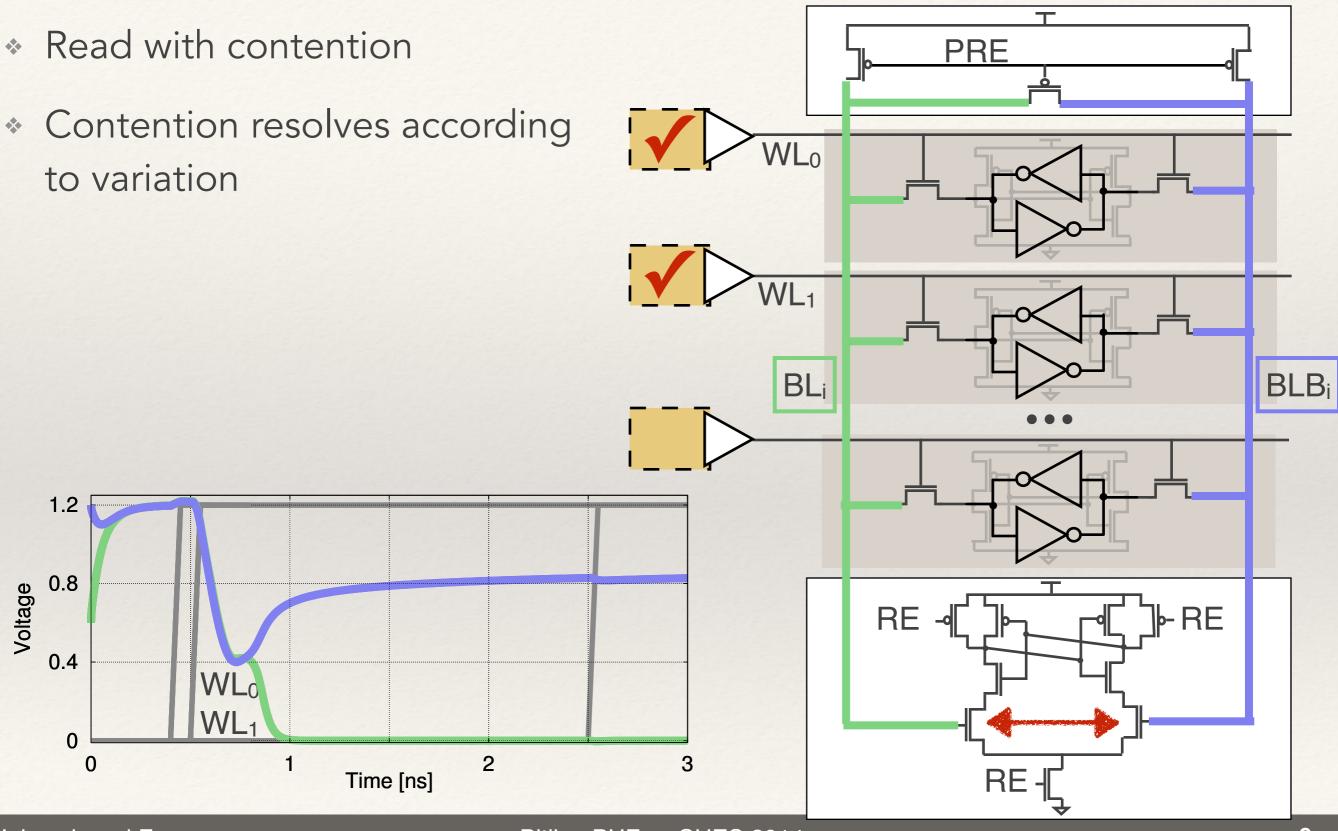
Holcomb and Fu

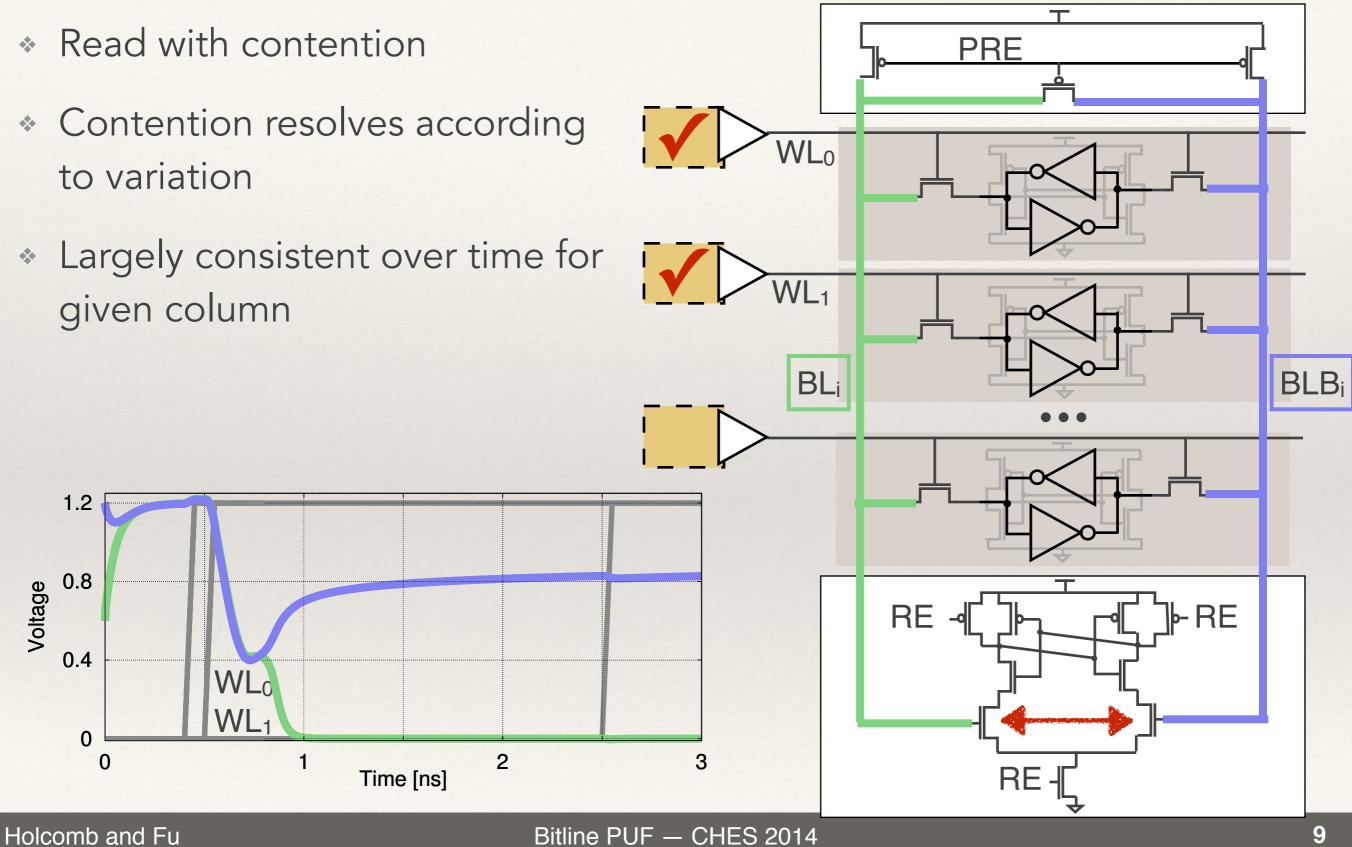










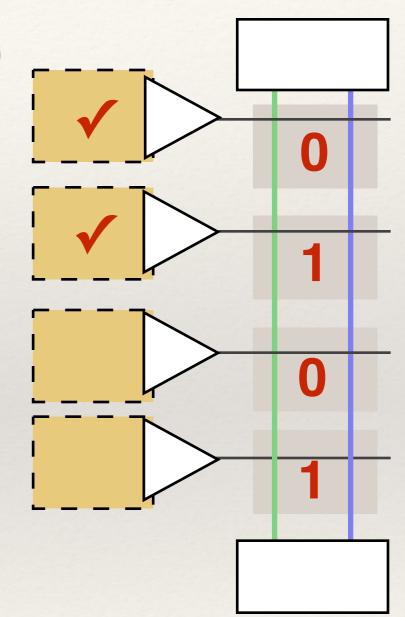


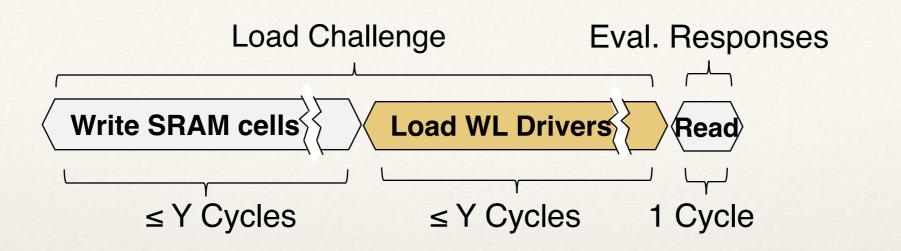
 Read with contention PRE Contention resolves according * WL₀ to variation Largely consistent over time for NL1 given column **BL**_i **BLB**_i Varies across columns or chips 1.2 0.8 Voltage - RE RE 0.4 M W 0 2 3 0 RE Time [ns]

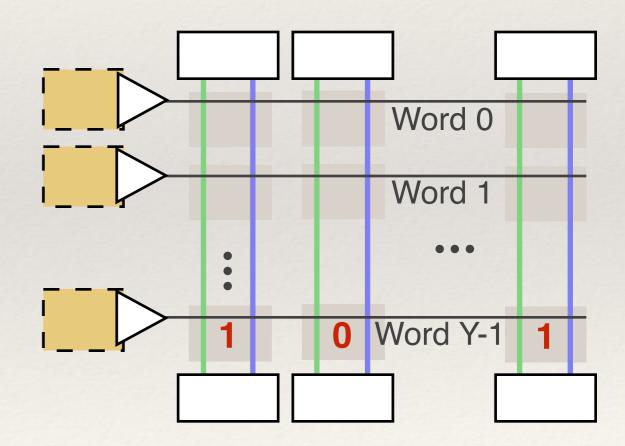
Bitline PUF - CHES 2014

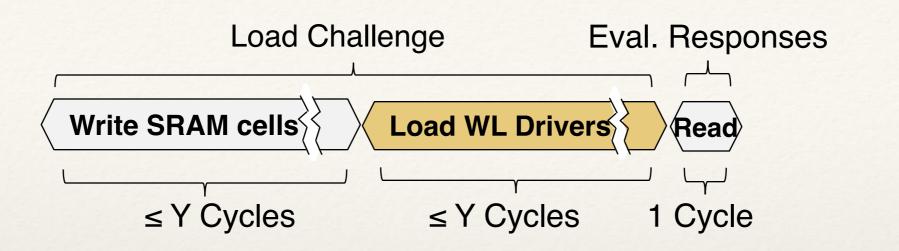
Challenge Response Pairs

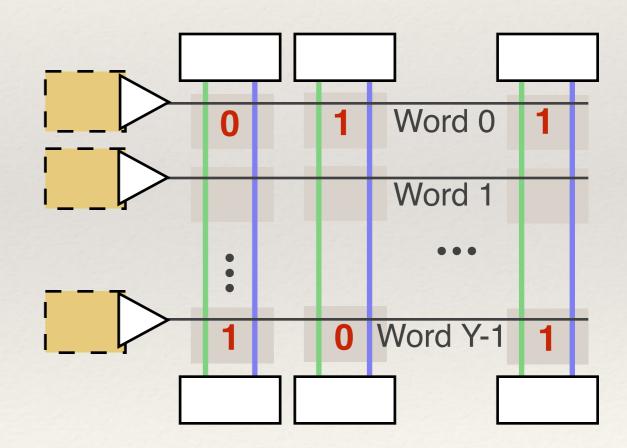
- PUF Challenge:
 - 4^Y possible challenges (Y = num. rows)
 - * For each cell in column:
 - 1. wordline on, cell value 0
 - 2. wordline on, cell value 1
 - 3. wordline off, cell value 0
 - 4. wordline off, cell value 1
- * PUF Response:
 - Value read by sense amp of column(s)

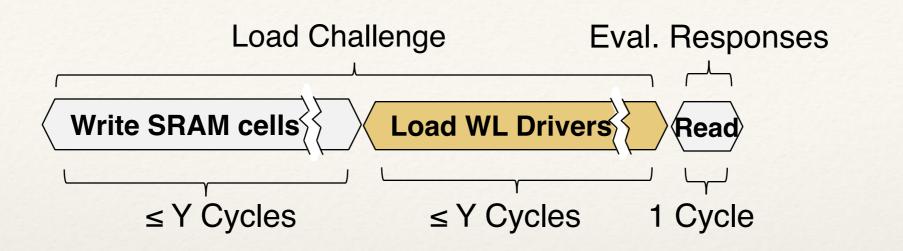


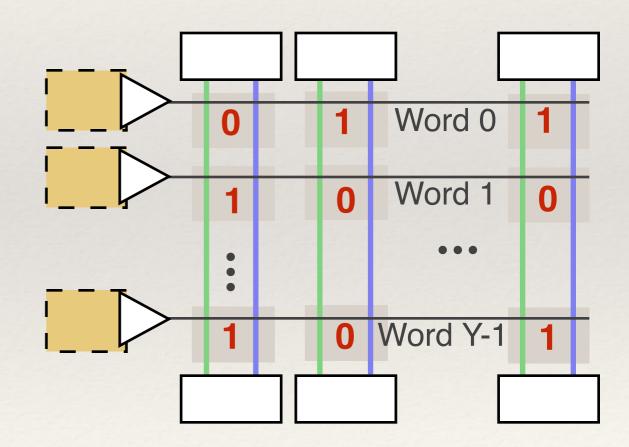


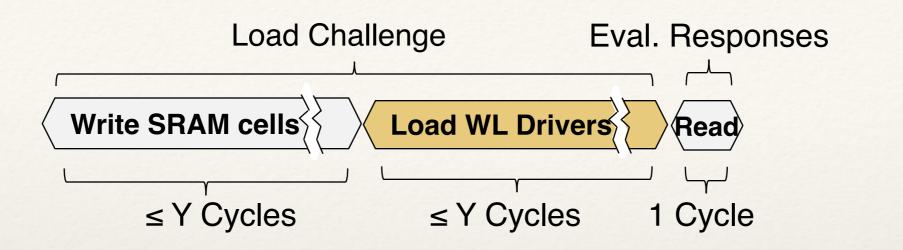


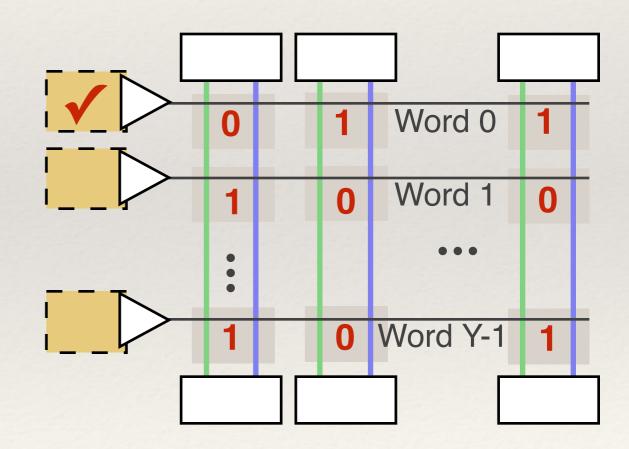


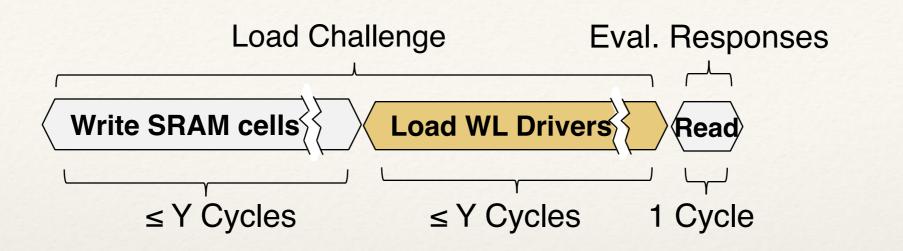


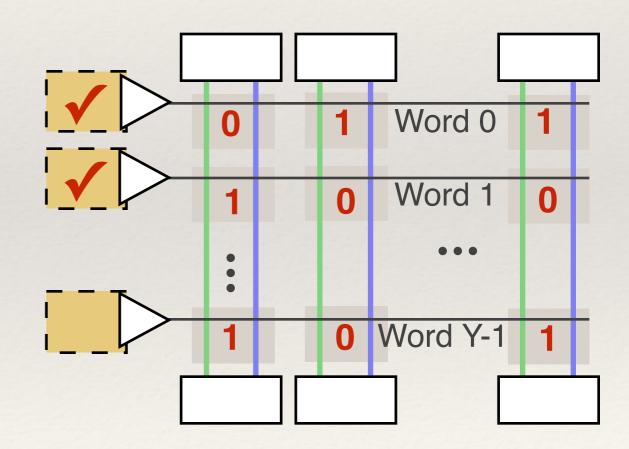


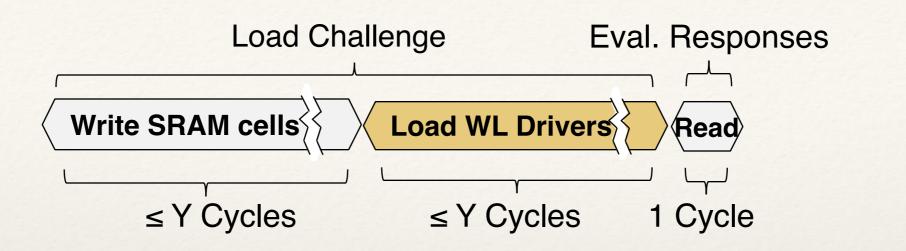


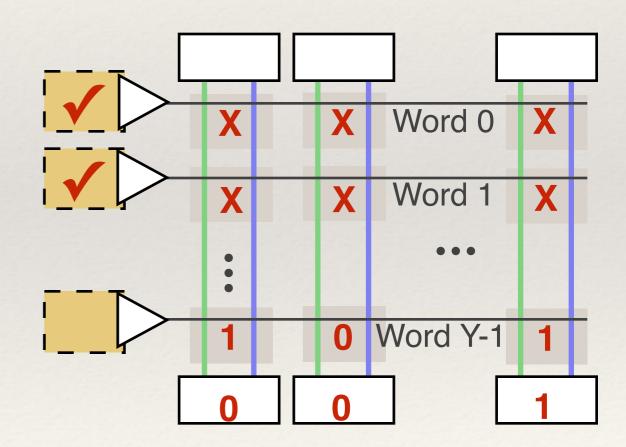


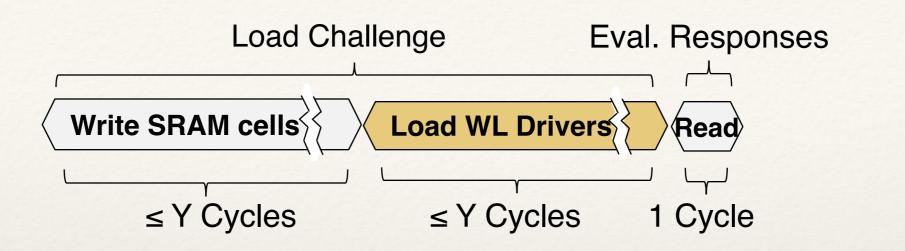


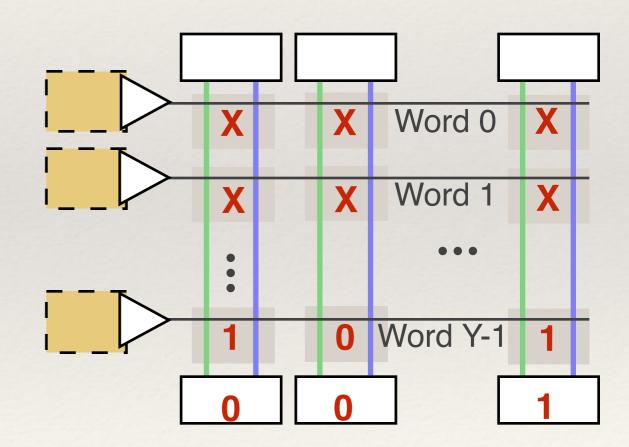


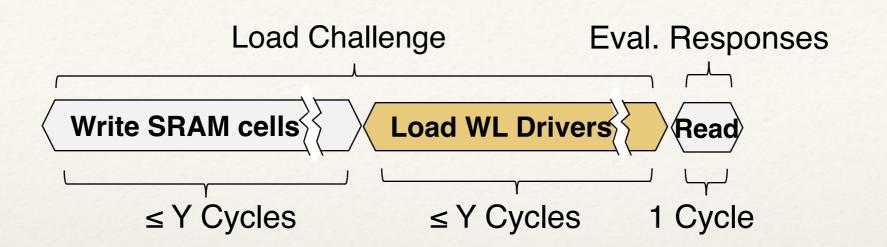




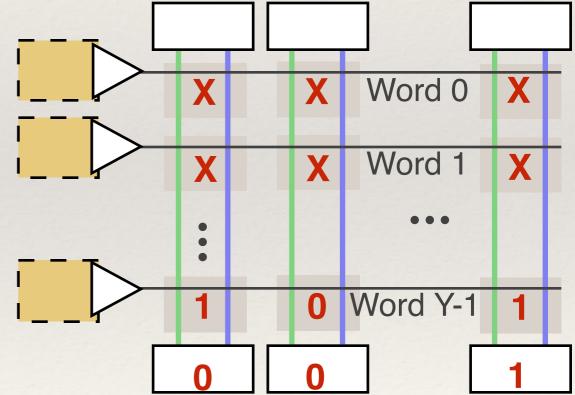


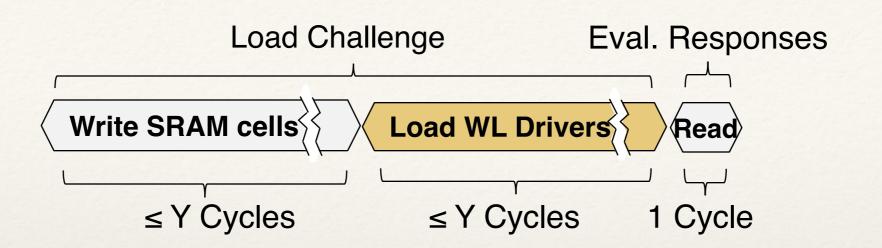




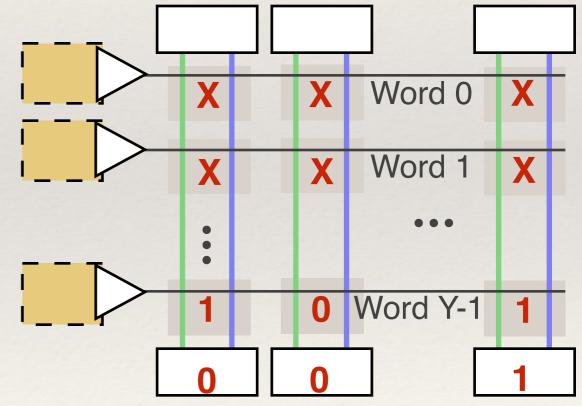


- Word-parallel (e.g. 256 columns)
- Response latency
 - 6 cycles for 256-bit response as shown
 - Depends on number of enabled rows



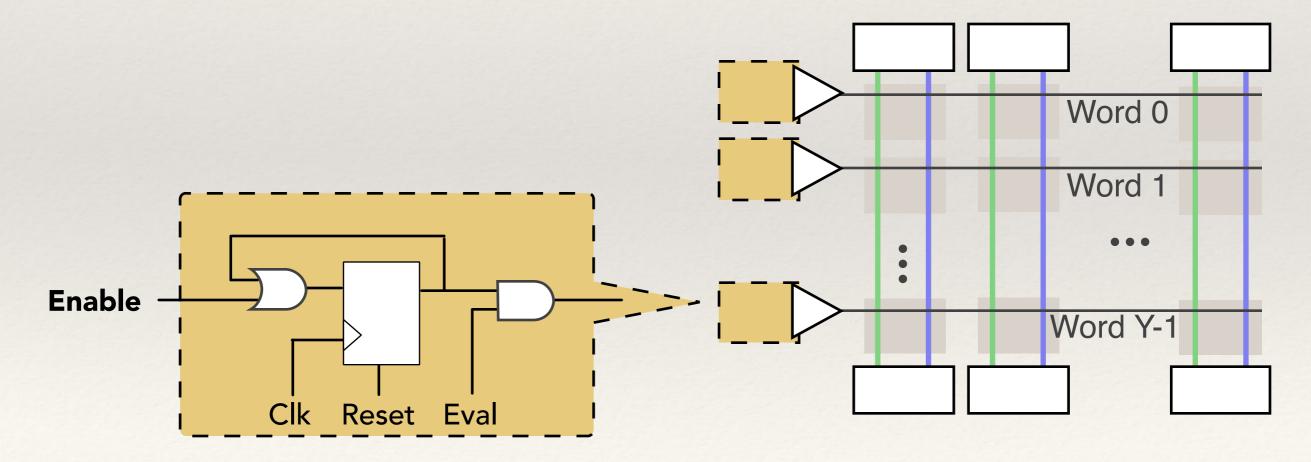


- Word-parallel (e.g. 256 columns)
- Response latency
 - 6 cycles for 256-bit response as shown
 - Depends on number of enabled rows
- Area overhead
 - A few extra gates per SRAM row
 - Don't need to add circuitry on all rows



Integration

- Simple digital interface
- No power-cycling required
- Non-exclusive, SRAM rows still usable as memory when not used for PUF
- Does not upset stored data in non-used rows

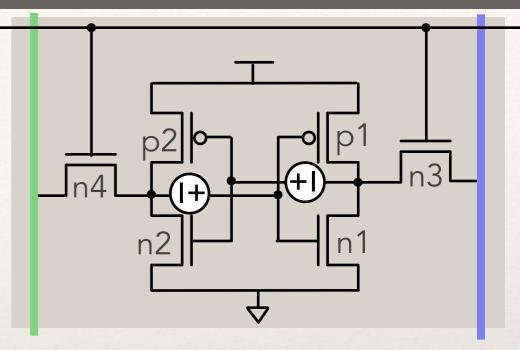


Outline

- 1. Introduction
 - PUFs
 - * SRAM
 - Bitline PUF
- 2. Evaluation
 - Uniqueness
 - Reliability
 - Modeling Attacks
- 3. Summary and Related work

Methodology

- Circuit simulation using Ngspice
- Devices are 90nm Predictive Technology Model [1]
- * Sizing according to Nii et al. [2]
- Variation: threshold voltage and channel length [3,4]
- Noise: between cross-coupled nodes [5]

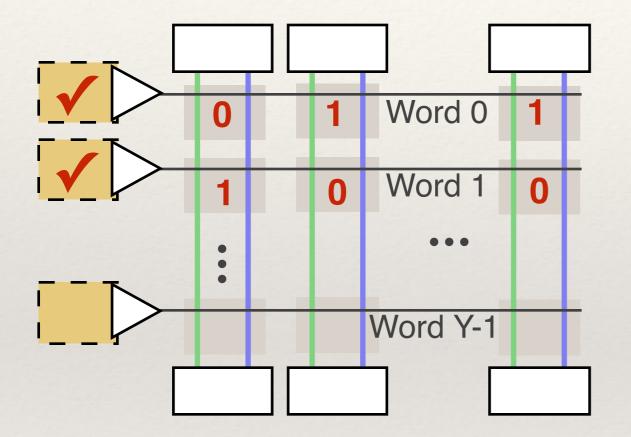


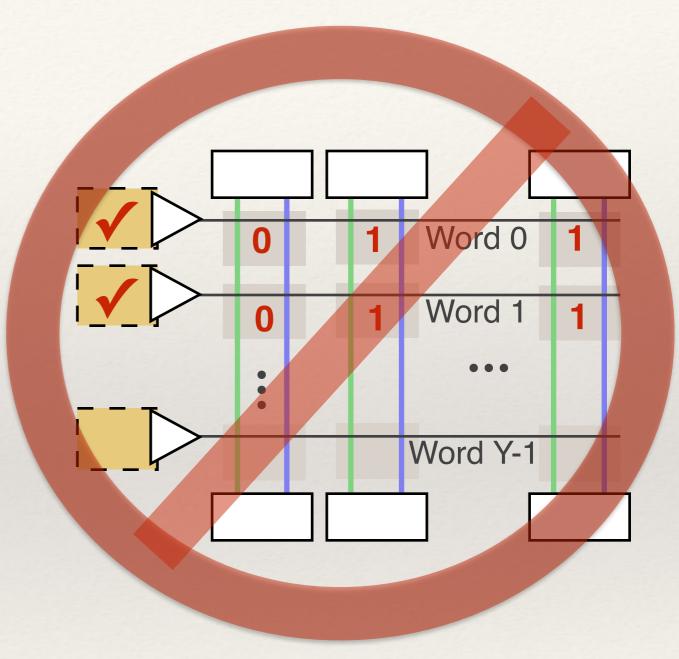
		Sizing		Process Variation			
		W [nm]	L [nm]	vth0 [mV]		lint [nm]	
				μ	σ	μ	σ
SRAM cell	n1,n2	200	90	397	13.4	7.5	3
	n3,n4	140	90	397	16.0	7.5	3
	p1,p2	140	90	-339	16.0	7.5	3
Sense Amp	NMOS	1000	90	397	6.0	7.5	3
& Precharge	PMOS	1000	90	-339	6.0	7.5	3

experiment code available online: https://github.com/danholcomb/bitline-puf

- [1] Predictive Technology Model. 90nm NMOS and PMOS BSIM4 Models
- [2] Nii et al., IEEE Journal of Solid State Circuits, 2004
- [3] Pelgrom et al. IEEE Journal of Solid State Circuits, 1989
- [4] Seevinck et al. IEEE Journal of Solid State Circuits, 1987
- [5] Anis et al. Workshop on System-on-Chip for Real-Time Applications, 2005

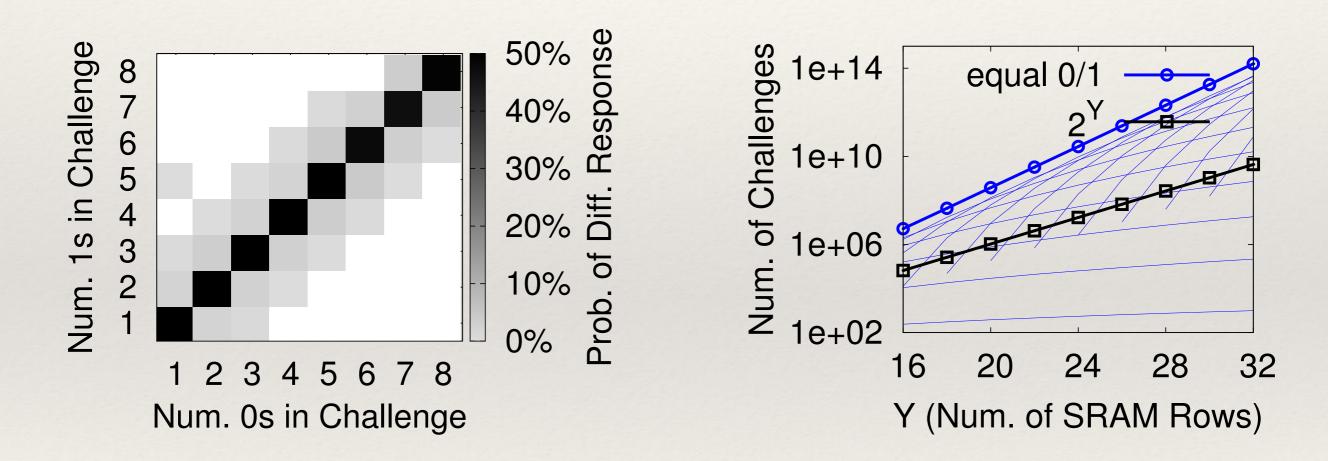
Choosing Useful Challenges





Choosing Useful Challenges

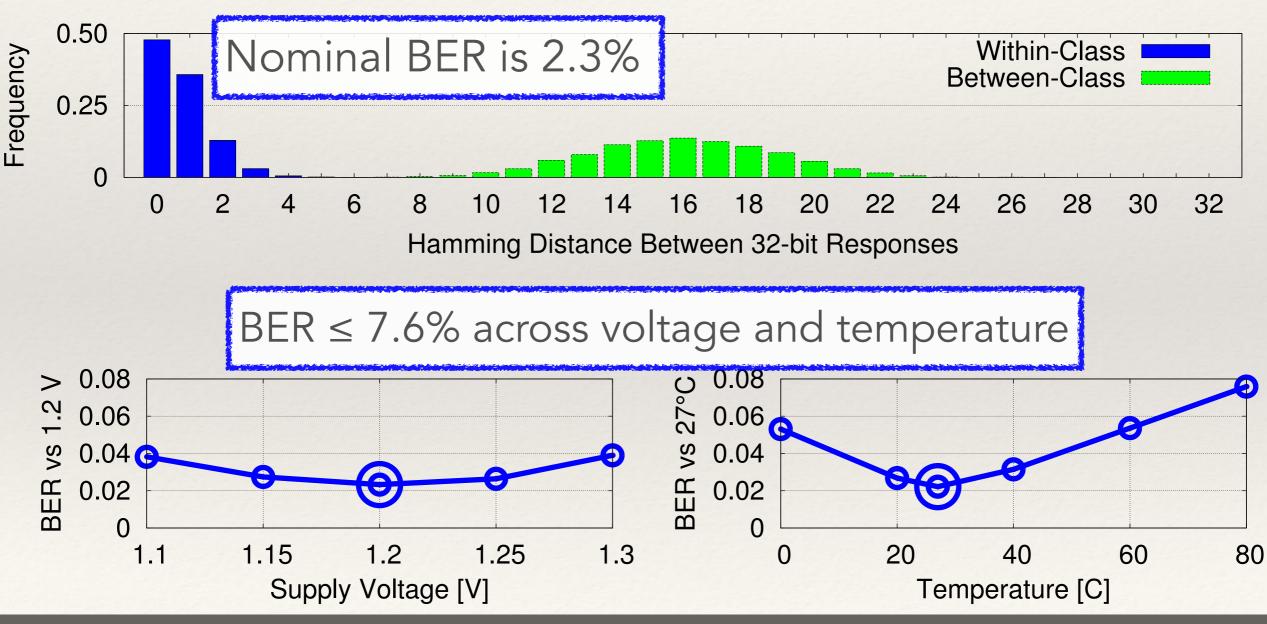
- Useful challenges have equal number of 0s and 1s
- Exponential subset of the 4^Y possible challenges



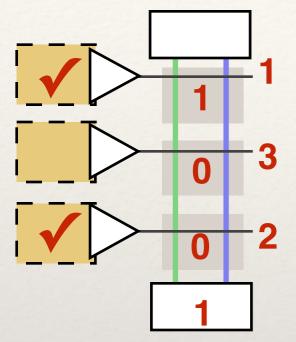
(Asymmetric designs may have different useful challenges)

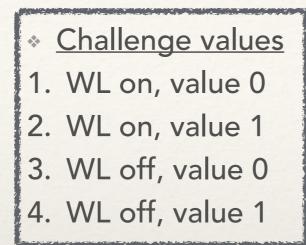
Uniqueness and Reliability

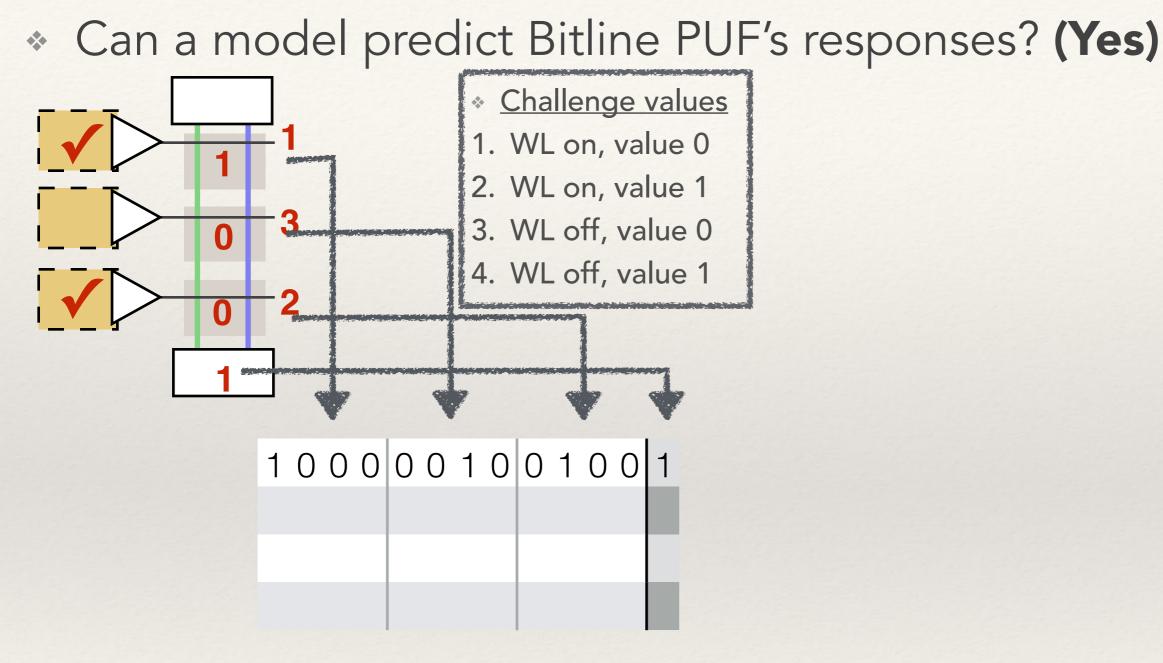
- Applying random challenges with equal number 0s and 1s
- Nominal conditions: 1.2V and 27°C

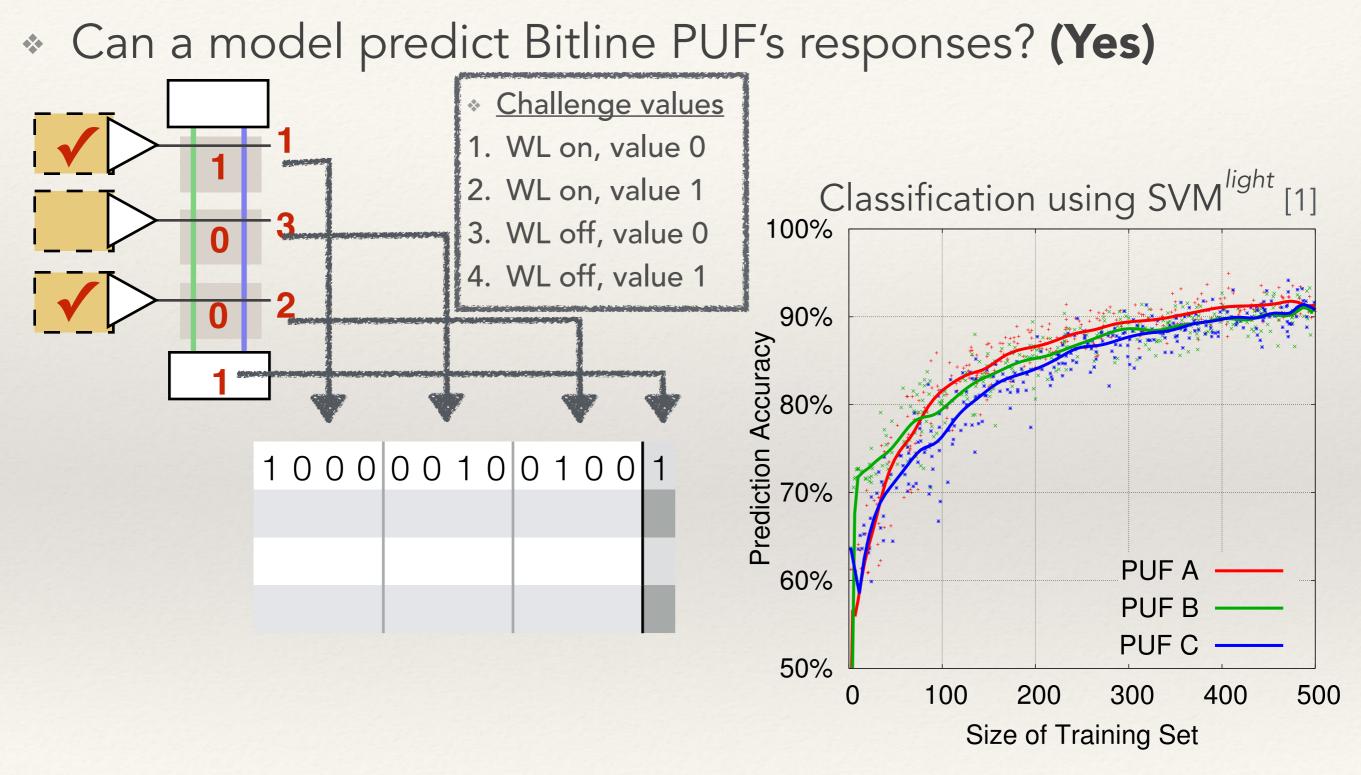


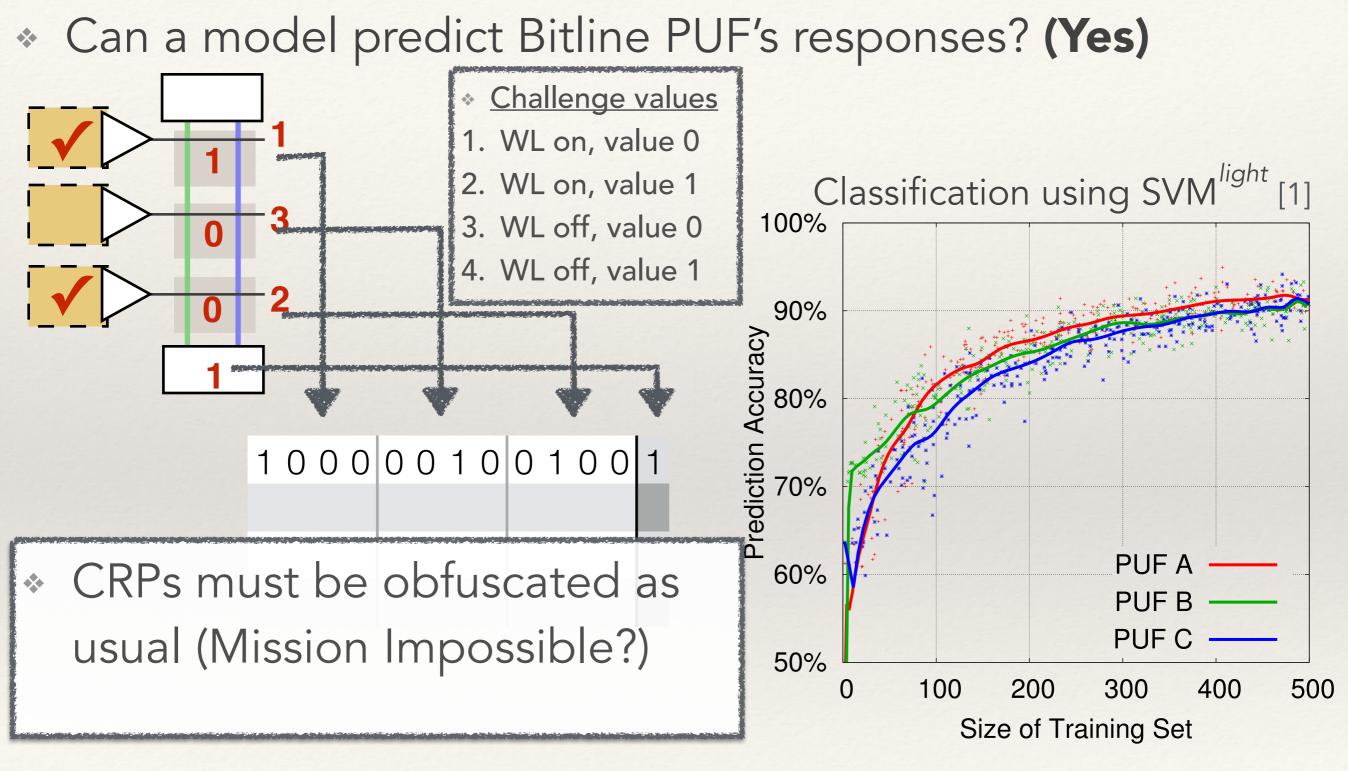
* Can a model predict Bitline PUF's responses? (Yes)











Outline

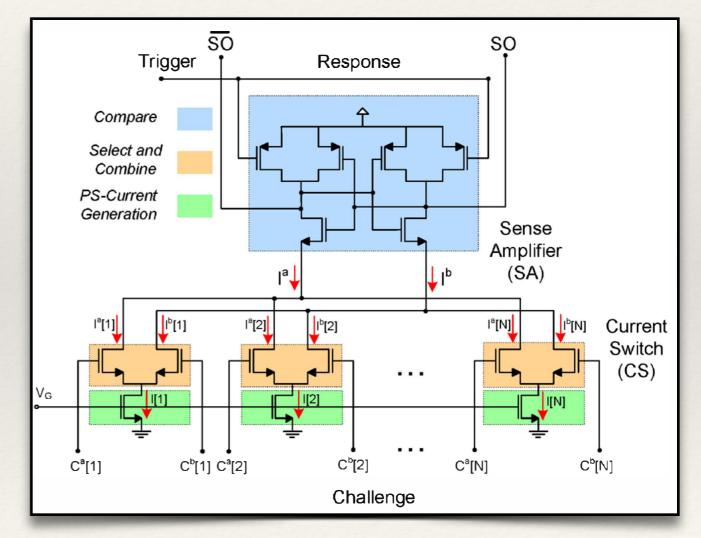
- 1. Introduction
 - PUFs
 - SRAM
 - Bitline PUF
- 2. Evaluation
 - Uniqueness
 - Reliability
 - Modeling Attacks

3. Summary and Related work

Related Work

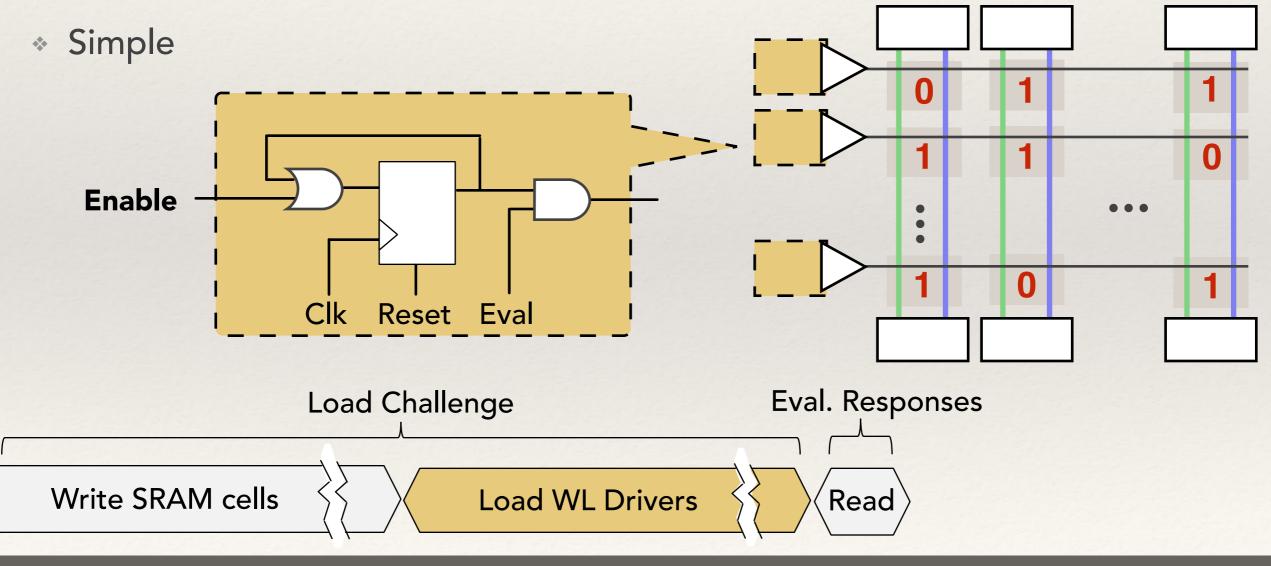
- * SRAM PUFs [1,2,3]
- Bistable-ring PUF [4]
- Low-power current PUF [5]

[1] Guajardo et al. CHES 2007
[2] Holcomb et al. T-Comp 2009
[3] Zheng et al. DAC 2013
[4] Chen et al. HOST 2011
[5] Majzoobi et al. ISCAS 2011



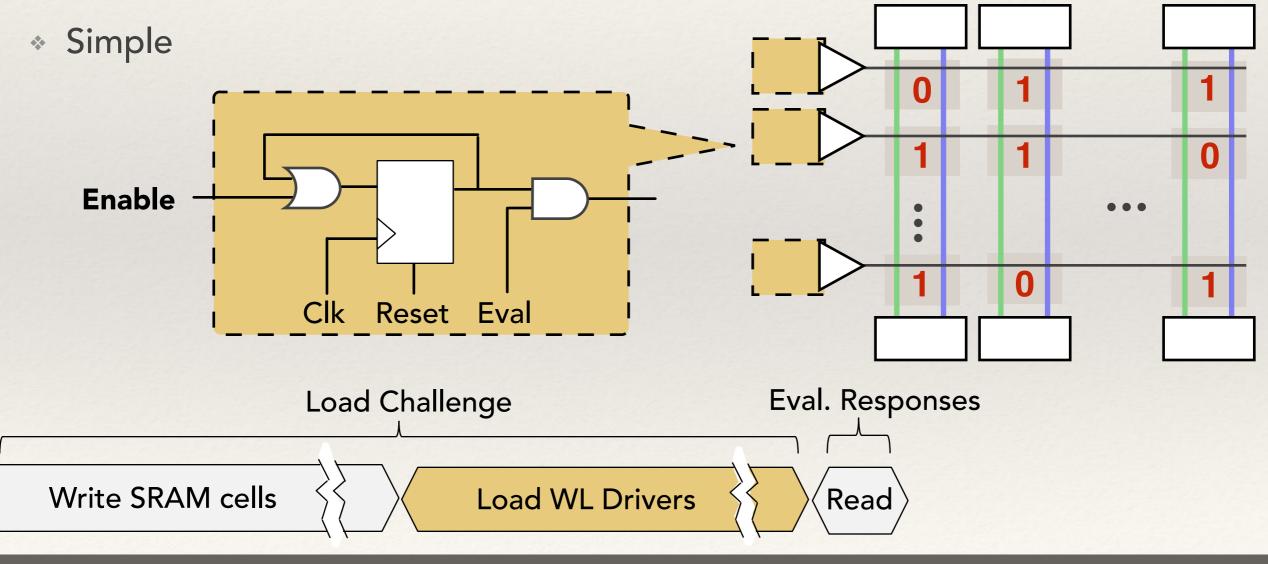
Bitline PUF: Summary

- Modifying wordline drivers of SRAM array creates a new PUF with desirable properties
 - Challenge-response operation
 - Low area overhead



Bitline PUF: Questions?

- Modifying wordline drivers of SRAM array creates a new PUF with desirable properties
 - Challenge-response operation
 - Low area overhead



Backup: Power Consumption

